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## Discrete POWER & Signal **Technologies**

## 2N5962

# **MMBT5962**





## **NPN General Purpose Amplifier**

This device is designed for use as low noise, high gain, general purpose amplifiers requiring collector currents to 50 mA. Sourced from Process 07. See 2N5088 for characteristics.

## **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
$V_{CEO}$	Collector-Emitter Voltage	45	V	
V <sub>CBO</sub>	Collector-Base Voltage	45	V	
V <sub>EBO</sub>	Emitter-Base Voltage	8.0	V	
Ic	Collector Current - Continuous	100	mA	
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C	

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

## **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	М	Units	
		2N5962	*MMBT5962	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

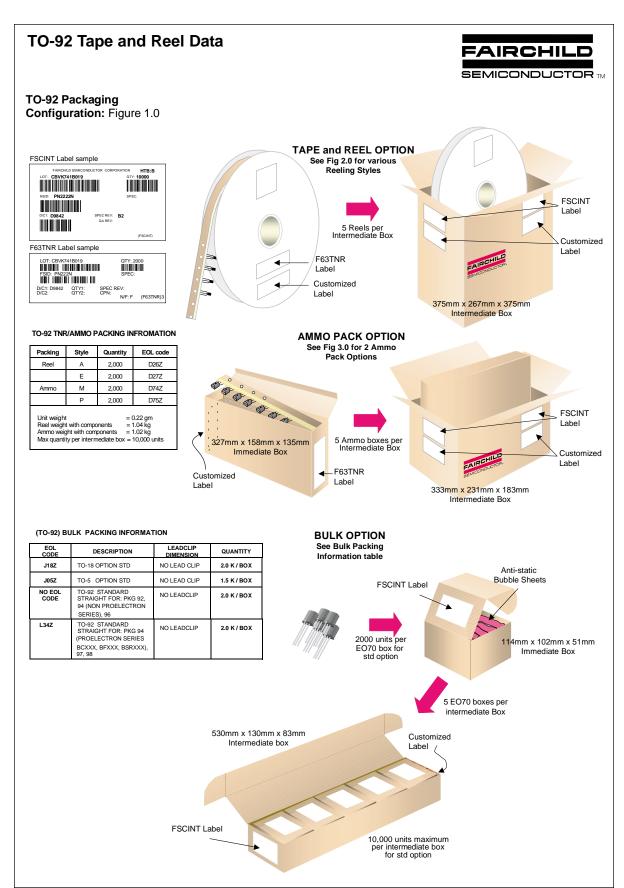
<sup>1)</sup> These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

# NPN General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Max	Units	
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_C = 5.0 \text{ mA}, I_B = 0$	45		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 10  \mu A, I_E = 0$	45		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	8.0		V
I <sub>сво</sub>	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$		2.0	nA
1	Freitter Cutoff Cumant	$V_{CB} = 30 \text{ V}, I_{E} = 0, T_{A} = 65 ^{\circ}\text{C}$		50	nA
EBO	Emitter Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		1.0	nA
ON CHAF	RACTERISTICS*				
h <sub>FE</sub>	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}$	450		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$	500		
		$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ mA}$	550 600	1400	
.,	Collector Emitter Seturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$	000	0.2	V
VOE (OOt)					
J <sub>BE(on)</sub>	Collector-Emitter Saturation Voltage  Base-Emitter On Voltage  SIGNAL CHARACTERISTICS	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
V <sub>BE(ON)</sub>	-	· ·	0.5		•
V <sub>BE(on)</sub> SMALL S	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$	0.5	0.7	V
SMALL S C <sub>cb</sub>	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$	0.5	4.0	V
SMALL S C <sub>cb</sub>	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	600	4.0	V
SMALL S C <sub>cb</sub>	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	600	4.0 6.0	V
V <sub>CE</sub> (sat) V <sub>BE</sub> (on)  SMALL S C <sub>cb</sub> C <sub>eb</sub> Ofe	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$		4.0 6.0	V
SMALL S Cob Cob	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ $V_{CB} = 5.0 \text{ V}$ $V_{EB} = 0.5 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$ $V_{CE} = 5.0 \text{ V}, I_{C} = 10 \text{ \muA},$ $R_{S} = 10 \text{ k}\Omega, f = 1.0 \text{ kHz},$	600	0.7 4.0 6.0 200	PF PF
SMALL S Cob Cob Tree Tree Tree Tree Tree Tree Tree Tre	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V} \\ V_{EB} &= 0.5 \text{ V} \\ \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ R_{S} &= 10 k\Omega, f = 1.0 \text{ kHz}, \\ B_{W} &= 400 \text{ Hz} \end{split}$	600	4.0 6.0	V
SMALL S Ccb Ceb	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}, \end{split}$	600	0.7 4.0 6.0 200	pF pF
SMALL S Ccb Ceb	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ V_{CB} &= 5.0 \text{ V} \\ V_{EB} &= 0.5 \text{ V} \\ \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 1.0 \text{ kHz} \\ I_{C} &= 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ R_{S} &= 10 k\Omega, f = 1.0 \text{ kHz}, \\ B_{W} &= 400 \text{ Hz} \end{split}$	600	0.7 4.0 6.0 200	pF pF
SMALL S Cob Cob Tree Tree Tree Tree Tree Tree Tree Tre	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ \end{aligned}$	600	0.7 4.0 6.0 200	PF PF
SMALL S Cob Cob Tree Tree Tree Tree Tree Tree Tree Tre	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \end{split}$	600	4.0 6.0 200 3.0 6.0	PF PF
SMALL S Cob Cob	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ \end{split}$	600	0.7 4.0 6.0 200	PF PF
SMALL S	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 k\text{Hz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \\ &R_{S} = 10 k\Omega, f = 1.0 k\text{Hz}, \end{split}$	600	4.0 6.0 200 3.0 6.0 4.0	PF PF dB dB dB
SMALL S Cob Cob Tree Tree Tree Tree Tree Tree Tree Tre	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ \end{split}$	600	4.0 6.0 200 3.0 6.0	PF PF
SMALL S  Cob  Cob  Tree  Tree	Base-Emitter On Voltage  SIGNAL CHARACTERISTICS  Collector-Base Capacitance  Emitter-Base Capacitance  Small-Signal Current Gain	$\begin{split} &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA} \\ &V_{CB} = 5.0 \text{ V} \\ &V_{EB} = 0.5 \text{ V} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 1.0 \text{ kHz} \\ &I_{C} = 10 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 10 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 1.0 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 10 k\Omega, f = 1.0 \text{ kHz}, \\ &B_{W} = 400 \text{ Hz} \\ &V_{CE} = 5.0 \text{ V}, \text{ I}_{C} = 100 \mu\text{A}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 k\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, f = 1.0 \text{ kHz}, \\ &R_{S} = 100 \text{ k}\Omega, \\ &R_{S} = 100 $	600	4.0 6.0 200 3.0 6.0 4.0	PF PF dB dB dB

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

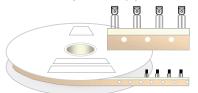


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## TO-92 Tape and Reel Data, continued

## **TO-92 Reeling Style** Configuration: Figure 2.0

## Machine Option "A" (H)



Style "A", D26Z, D70Z (s/h)

# Machine Option "E" (J)

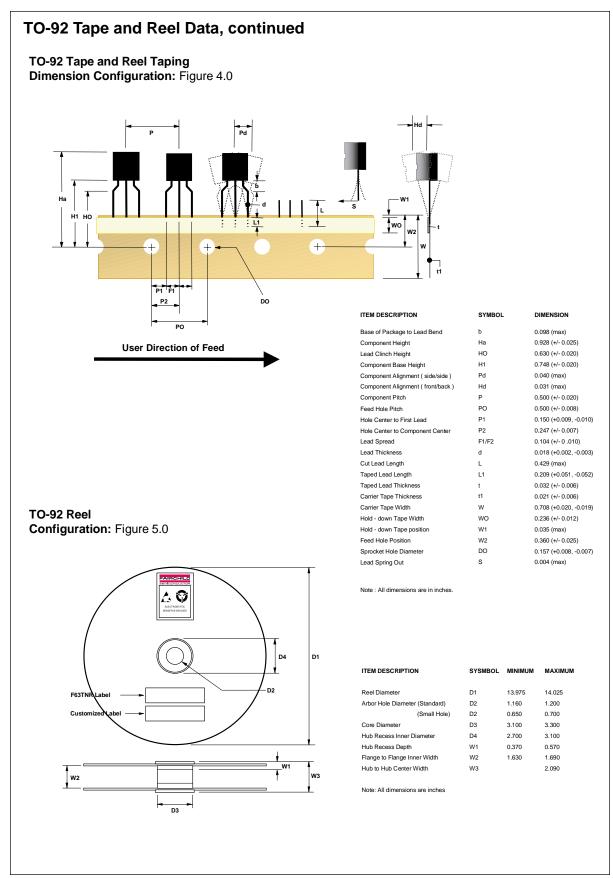
Style "E", D27Z, D71Z (s/h)

## **TO-92 Radial Ammo Packaging** Configuration: Figure 3.0





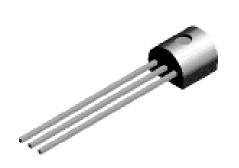
FIRST WIRE OFF IS COLLECTOR (ON PKG. 92) ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

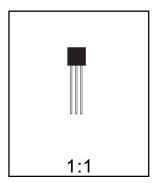


# **TO-92 Package Dimensions**



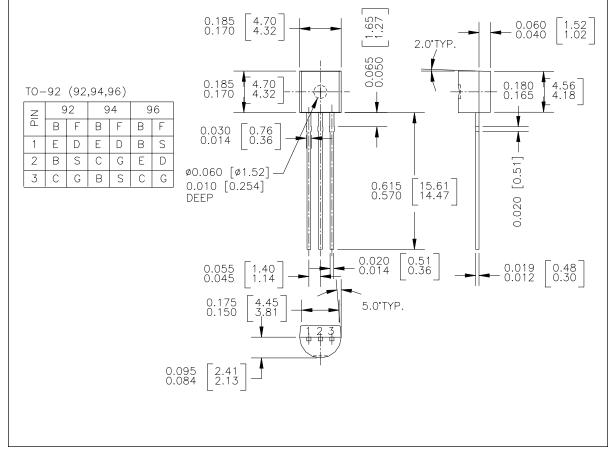
# TO-92 (FS PKG Code 92, 94, 96)





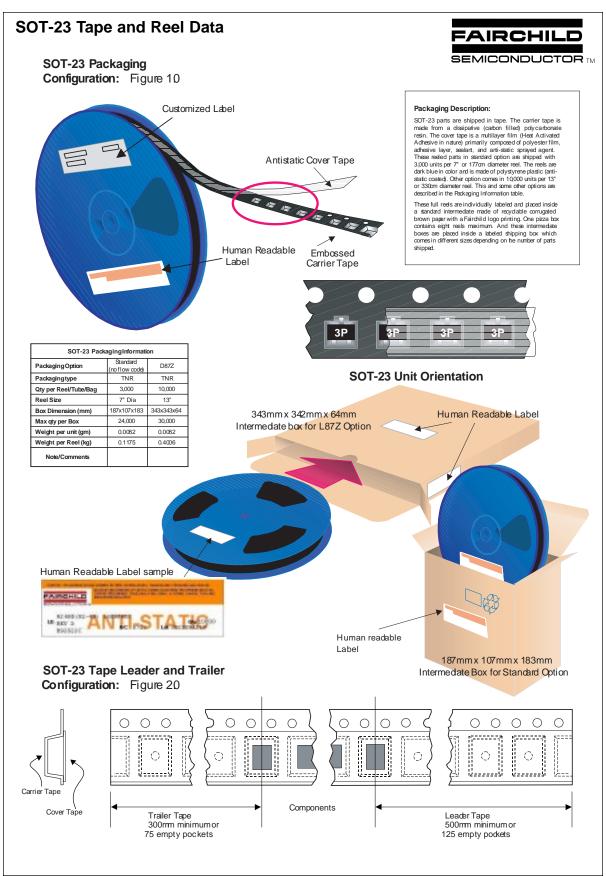
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977



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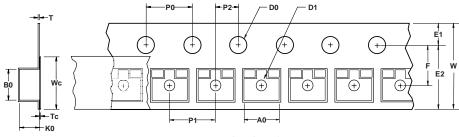
January 2000, Rev. B



## SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



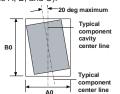
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation



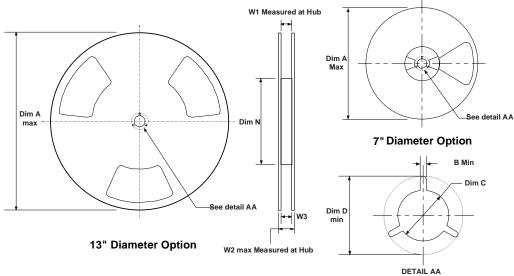
Sketch B (Top View)
Component Rotation



Sketch C (Top View)

Component lateral movement

# **SOT-23 Reel Configuration:** Figure 4.0

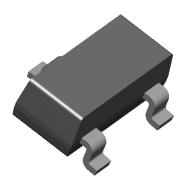


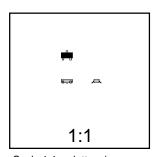
	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

## **SOT-23 Package Dimensions**



# SOT-23 (FS PKG Code 49)

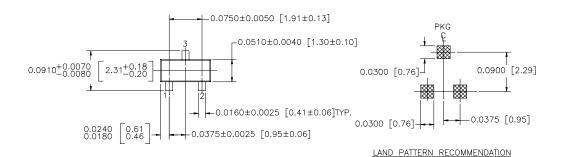


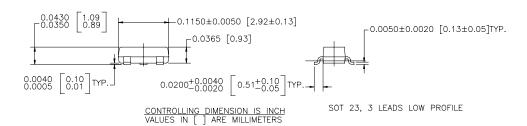


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO -236, VARIATION AB, ISSUE G, DATED JUL 1993

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